

ABSTRACT OF THE DISCLOSURE

A method of forming a cap film comprises a first polishing step of performing a polishing operation at selectivity of R_1 (= removal rate for the cap film/removal rate for the insulating film), and a
5 second polishing step of performing a polishing operation at selectivity of R_2 (= removal rate for the cap film/removal rate for the insulating film). Each of the polishing operations is performed by using a
10 slurry having the condition of $R_1 > R_2$. By performing the polishing operations at different selectivity, the cap film free from problems such as dishing of the cap film and the residual cap film on side walls of a recess is formed. Consequently, a semiconductor device
15 having an excellent RC characteristic can be provided.